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October 2016

FFSH20120ADN_F155 Silicon Carbide Schottky Diode 1200 V, 20 A

Features

- Max Junction Temperature 175 °C
- · Avalanche Rated 100 mJ
- · High Surge Current Capacity
- · Positive Temperature Coefficient
- · Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

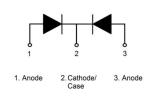
Applications

- · General Purpose
- · SMPS, Solar Inverter, UPS
- · Power Switching Circuits

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.





Absolute Maximum Ratings T_C = 25 °C unless otherwise noted. (per leg)

Symbol	Parameter	Ratings	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage		1200	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)		100	mJ
I _F	Continuous Rectified Forward Current @ Tc < 148 °C		10* / 20**	Α
I _{F, Max}		T _C = 25 °C, 10 μs	630	Α
		T _C = 150 °C, 10 μs	560	Α
I _{F,SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	96	Α
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	46	Α
Ptot	Dower Dissination	T _C = 25 °C	150	W
	Power Dissipation	T _C = 150 °C	25	W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
	TO247 Mounting Torque, M3 Screw		60	Ncm

Thermal Characteristic

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	1* / 0.44**	°C/W

^{*} Per leg, ** Per Device

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSH20120ADN_F155	FFSH20120ADN	TO-247 Long Lead	Tube	N/A	N/A	30 units

Electrical Characteristics T_C = 25 °C unless otherwise noted. (per leg)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _F	Forward Voltage	I _F = 10 A, T _C = 25 °C	-	1.45	1.75	V
		I _F = 10 A, T _C = 125 °C	-	1.7	2	
		I _F = 10 A, T _C = 175 °C	-	2	2.4	
I _R	Reverse Current	V _R = 1200 V, T _C = 25 °C	-	-	200	μА
		$V_R = 1200 \text{ V}, T_C = 125 ^{\circ}\text{C}$	-	-	300	
		$V_R = 1200 \text{ V}, T_C = 175 ^{\circ}\text{C}$	-	-	400	
Q_C	Total Capacitive Charge	V = 800 V	-	62	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	612	-	pF
		$V_R = 400 \text{ V}, f = 100 \text{ kHz}$	-	58	-	
		$V_R = 800 \text{ V}, f = 100 \text{ kHz}$	-	47	-	

Typical Characteristics T_J = 25 °C unless otherwise noted (per leg).

Figure 1. Forward Characteristics

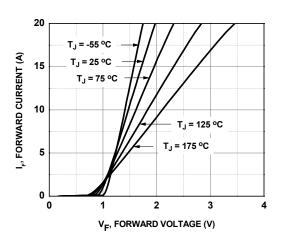


Figure 3. Reverse Characteristics

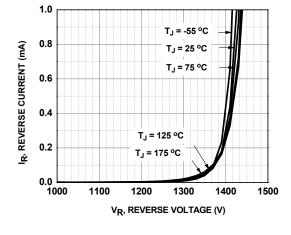


Figure 2. Reverse Characteristics

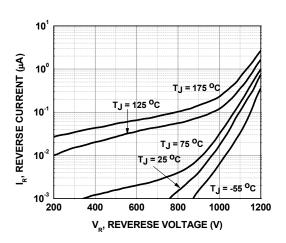
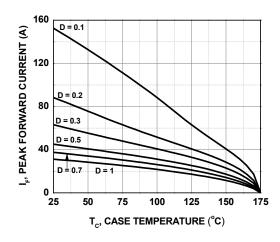


Figure 4. Current Derating



Notes: 1: EAS of 100 mJ is based on starting T_J = 25 °C, L = 0.5 mH, I_{AS} = 20 A, V = 150 V.

Typical Characteristics $T_J = 25$ °C unless otherwise noted (per leg, continue).

Figure 5. Power Derating

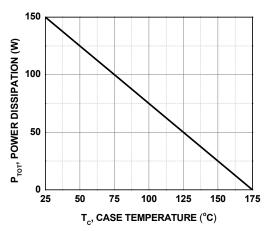
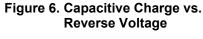


Figure 7. Capacitance vs. Reverse Voltage



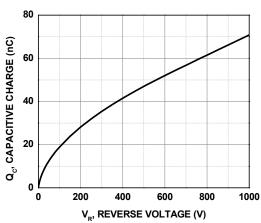
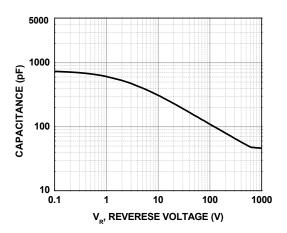


Figure 8. Capacitance Stored Energy



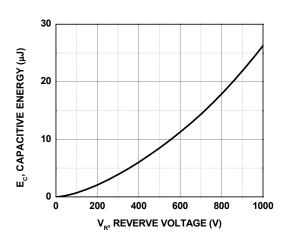
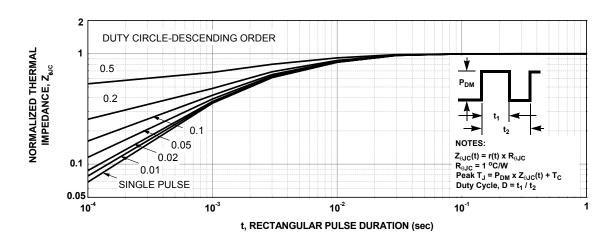
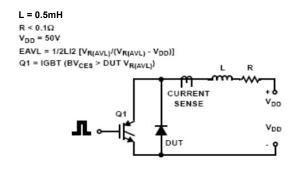


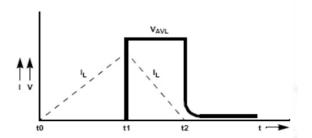
Figure 9. Junction-to-Case Transient Thermal Response Curve

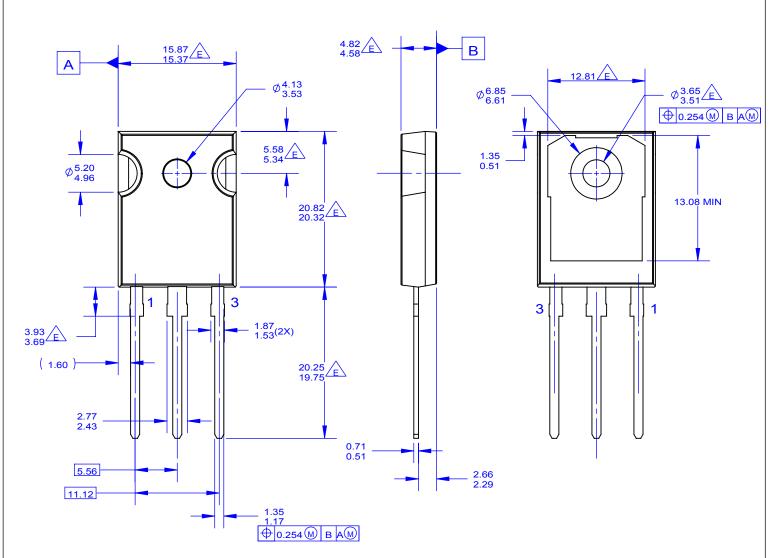


Test Circuit and Waveforms

Figure 10. Unclamped Inductive Switching Test Circuit & Waveform







NOTES: UNLESS OTHERWISE SPECIFIED.

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- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 1994





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